

On page 6, line 17, change "1-6" to --1--;

On page 7, line 13, change "terminals" to --terminal regions--;

On page 7, line 19, change "ends" to --regions--;

On page 8, line 18, change "illustrate" to --illustrated--;

On page 8, line 25, insert a comma after ("BPSG");

On page 10, line 1, change "FIG. 7" to --FIG. 6--;

On page 10, line 3, insert a comma after "net" and delete the comma after "process";

On page 10, line 4, insert a comma after "dry" and delete the comma after "process";

On page 10, line 12, change "process" to --processes--; and

On page 11, line 3, after "entireties" insert a comma and before the period insert --may be used to form layer 16--.

IN THE CLAIMS:

In claim 17, line 10, after "which" change "are" to --is--;

In claim 17, line 11, delete "said layer of";

In claim 21, line 2, before "selected" insert --said--;

In claim 30, line 2, after "said" insert --selected regions of said--; and

In claim 31, line 2, before "layer" insert --selected regions of said--.

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34. (amended) A semiconductor device, comprising:

an insulating substrate;

at least two [spaced apart regions] discrete portions of polysilicon disposed over the insulating substrate; and

a metal silicide fuse comprising a central region disposed adjacent the insulating substrate and between said at least two [spaced apart regions] discrete portions and at least two terminal regions disposed on said at least two [spaced apart regions] discrete portions of polysilicon and on each end of said central region.

In claim 36, line 2, after "oxide" insert --region--.

a³ 39. (amended) The semiconductor device of claim 34, further comprising a layer of dielectric material disposed between said metal silicide fuse and said at least two [spaced apart polysilicon regions] discrete portions.

a⁴ 44. (amended) The semiconductor device of claim 34, wherein said at least two [spaced apart regions] discrete portions of polysilicon [comprises] comprise doped polysilicon.

In claim 48, line 3, change "spaced apart regions" to --discrete portions--;

In claim 50, line 7, delete "at least two";

In claim 54, line 1, change "claim 51" to --claim 53--;

In claim 60, line 2, delete "at least two";

In claim 65, line 2, after "said" insert --selected regions of said--;

In claim 68, line 1, after "defining" insert --said--; and

In claim 68, line 2, after "and" change "a" to --said--.

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a⁵ 71. (amended) A method of substantially simultaneously fabricating a gate and a fuse on a semiconductor substrate, comprising:

disposing a layer of insulative material over at least an exposed region of the semiconductor substrate;

disposing a layer of polysilicon over the semiconductor [device] substrate, including over said layer of insulative material and over field oxide regions disposed on the semiconductor substrate;

patterning at least regions of said layer of polysilicon disposed [on] over at least one field oxide region of said field oxide regions;

disposing a layer of metal silicide on said layer of polysilicon;

patterning at least said layer of metal silicide to define the fuse and the gate therefrom.

a⁶ 73. (amended) The method of claim 71, wherein said patterning said at least regions comprises defining at least two spaced apart regions of polysilicon on said at least one field oxide region and between which [said] a portion of said at least one field oxide region is exposed.

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a⁷ 98. (amended) The method of claim 97, wherein said removing said exposed regions of said layer of insulative material comprises etching said exposed regions of said layer of insulative material.

99. (amended) The method of claim 98, wherein said etching comprises dry etching said exposed regions of said layer of insulative material.

100. (amended) The method of claim 98, wherein said [removing] etching comprises anisotropically etching said exposed regions of said layer of insulative material.

In claim 101, line 2, change "gate" to --drain--.

IN THE DRAWINGS:

Accompanying this Preliminary Amendment is a Letter to the Chief Draftsman submitting proposed revisions to FIG. 4. Approval of the revised figure is respectfully requested.